D		Synapse		
Туре	current synapse with $\alpha$ -function shaped postsynaptic currents (PSCs)			
Dynamics	input current: $I(t) = \sum_{i} h(t - t_i)$			
	with kernel $h(t) = I_0 \frac{t}{\tau} e^{1-(t-t_i)/\tau} \theta(t-t_i)$			
	where $t_i$ is the arrival time of presynaptic spike <i>i</i> , $\theta$ is Heaviside step			
	function, with time constant $\tau$ and amplitude $I_0 = I_e$ , $I_i$ for excitatory			
	and inhibitory synapses respectively			
Parameters	$ au$ , $I_e$ , $I_i$			
E Input				
Poissonian input				
Uncorrelated	each cell receives $n_{syn}$ independent excitatory inputs generated by Pois-			
input	sonian point processes with rate <i>r<sub>syn</sub></i>			
Correlated	each cell receives $n_{syn}$ excitatory inputs drawn (without resampling)			
input	from a finite-sized pool (size $n_{pool}$ ) of independent Poissonian point processes with rate $r_{syn}$ resulting in correlation $c_{in} = n_{syn}/n_{pool}$ between			
	total input current of different cells			
Synapse	synapses placed on dendrites in certain layers depending on synaptic			
placement	input region (apical/homogeneous/basal) and cell type:			
	cell type	apical	homogeneous	basal
	cell type	apical upper half of L23	0	basal lower half of L23
		•	0	
	L3	•	L1 and L23	
	L3 L4 L5 Random plac	upper half of L23 - L1 and L23 cement of synapses v	L1 and L23 L4 all layers within allowed bour	lower half of L23 - L5 and L6 ndaries with uniform
	L3 L4 L5 Random plac	upper half of L23 - L1 and L23 cement of synapses v respect to membrar	L1 and L23 L4 all layers within allowed bour	lower half of L23 - L5 and L6 ndaries with uniform
Parameters	L3 L4 L5 Random plac density with	upper half of L23 - L1 and L23 cement of synapses v respect to membrar ion)	L1 and L23 L4 all layers within allowed bour	lower half of L23 - L5 and L6 ndaries with uniform
Parameters	L3 L4 L5 Random plac density with of input reg	upper half of L23 - L1 and L23 cement of synapses v respect to membrar ion)	L1 and L23 L4 all layers within allowed bour ne area (note: <i>n<sub>syn</sub></i>	lower half of L23 - L5 and L6 ndaries with uniform
Parameters	L3 L4 L5 Random plac density with of input reg	upper half of L23 - L1 and L23 cement of synapses v respect to membrar ion)	L1 and L23 L4 all layers within allowed bour ne area (note: <i>n<sub>syn</sub></i>	lower half of L23 - L5 and L6 ndaries with uniform
Parameters F Type	L3 L4 L5 Random plac density with of input regi n <sub>syn</sub> , r <sub>syn</sub> , c <sub>ir</sub>	upper half of L23 L1 and L23 cement of synapses v respect to membrar ion) Measuremen Simulated LFI field potentials (re	L1 and L23 L4 all layers within allowed bour ne area (note: <i>n<sub>syn</sub></i> ts	lower half of L23 - L5 and L6 ndaries with uniform is fixed irrespective
F	L3 L4 L5 Random plac density with of input reginsyn, r <sub>syn</sub> , c <sub>ir</sub> extracellular the line-sour extracellular	upper half of L23 L1 and L23 cement of synapses v respect to membrar ion) Measuremen Simulated LFI field potentials (re	L1 and L23 L4 all layers within allowed bour ne area (note: <i>n<sub>syn</sub></i> ts <i>P</i> presenting the LF I to be purely resist	lower half of L23 - L5 and L6 ndaries with uniform is fixed irrespective P) calculated using ive (non-capacitive)
F Type Assumptions Electrode	L3 L4 L5 Random plac density with of input reginsyn, rsyn, cir nsyn, rsyn, cir extracellular the line-sour extracellular and inifitely- ideal (non-fi	upper half of L23 L1 and L23 cement of synapses w respect to membrar ion) Measurement Simulated LFM field potentials (re- rce method medium as assumed -volumed with extra- ltering) point electro	L1 and L23 L4 all layers within allowed bour ne area (note: <i>n<sub>syn</sub></i> ts <i>P</i> presenting the LF I to be purely resist cellular conductivit ode placed either	lower half of L23 - L5 and L6 indaries with uniform is fixed irrespective P) calculated using ive (non-capacitive) ty $\sigma_{cond}$ in the center ( $r=0$ )
F Type Assumptions	L3 L4 L5 Random place density with of input regins n <sub>syn</sub> , r <sub>syn</sub> , c <sub>ir</sub> extracellular the line-sour extracellular and inifitely- ideal (non-fited)	upper half of L23 - L1 and L23 cement of synapses v respect to membrar ion) Measuremen Simulated LFI field potentials (re rce method medium as assumed -volumed with extra	L1 and L23 L4 all layers within allowed bour ne area (note: <i>n<sub>syn</sub></i> ts <i>P</i> presenting the LF l to be purely resist cellular conductivit ode placed either ffset by some dista	lower half of L23 - L5 and L6 indaries with uniform is fixed irrespective P) calculated using ive (non-capacitive) ty $\sigma_{cond}$ in the center ( $r=0$ ) ance; at depths cor-